

In re: David B. Slater, Jr. et al.
Serial No.
Filed: Concurrently Herewith
Page 3

Please insert the following Abstract.

Abstract

A semiconductor device is disclosed that includes a semiconductor substrate having a first surface and a second surface and a first conductivity type and at least one epitaxial layer on the first surface of the semiconductor substrate. The epitaxial layer is formed of a material with a dissociation temperature below that of the semiconductor substrate. A zone of increased carrier concentration is in the semiconductor substrate and extends from the second surface of the semiconductor material toward the first surface. A layer of metal is deposited on the second surface of the semiconductor substrate and forms an ohmic contact at the interface of the metal and the zone of increased carrier concentration.